

IN THE SPECIFICATION

Please replace the title of the invention with the following:

✓ ---METHOD OF PRODUCING A TRENCH CAPACITOR WITH ISOLATION
COLLAR---

IN THE CLAIMS

Please amend the claims as follows (a marked-up copy of the amended claim is attached hereto):

14. (Amended - Clean copy) A method for producing a trench capacitor, for use in a semiconductor memory cell, the method comprising:

forming a trench in a semiconductor substrate;

providing a first and a second conducting capacitor plate in the trench;

providing a dielectric layer as a capacitor dielectric between the first and the second conducting capacitor plates;

forming an isolation collar in an upper region of the trench;

+ filling a conducting filling material into the trench;

providing a first metal electrode layer on the dielectric layer inside the trench as the second conducting capacitor plate;

+ providing a second metal electrode layer in the upper region of the trench such that the second metal electrode layer is in electrical connection with the first metal electrode layer,